

NPN SILICON GERMANIUM RF TRANSISTOR

NESG240033

NPN SiGE RF TRANSISTOR FOR UHF-BAND, LOW NOISE, LOW DISTORTION AMPLIFICATION 3-PIN MINIMOLD (33 PKG)

FEATURES

- The device is an ideal choice for low noise, low distortion amplification.
 - NF = 0.75 dB TYP. @ $V_{CE} = 5 \text{ V}$, $I_{C} = 15 \text{ mA}$, f = 1 GHz
- Po (1 dB) = 23.5 dBm TYP. @ $V_{CE} = 5 \text{ V}$, Ic (set) = 40 mA, f = 1 GHz
- OIP3 = 35.5 dBm TYP. @ $V_{CE} = 5 V$, $I_{C (set)} = 40 mA$, f = 1 GHz
- Maximum stable power gain: MSG =13.0 dB TYP. @ VcE = 5 V, Ic = 40 mA, f = 1 GHz
- SiGe HBT technology (UHS2): f_T = 10.5 GHz
- This product is improvement of ESD of NESG2xxx series.
- 3-pin minimold (33 PKG)

ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Supplying Form
NESG240033	NESG240033-A	3-pin minimold (33 PKG) (Pb-Free)	'	8 mm wide embossed taping Pin 3 (Collector) face the perforation side
NESG240033-T1B	NESG240033-T1B-A		3 kpcs/reel	of the tape

Remark To order evaluation samples, please contact your nearby sales office. Unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25$ °C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vcво	5.5	V
Collector to Emitter Voltage	Vces	13	V
Collector to Emitter Voltage	Vceo	5.5	V
Base Current Note 1	Ів	36	mA
Collector Current	lc	400	mA
Total Power Dissipation	Ptot Note 2	480	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

Notes 1. Depend on the ESD protect device.

2. Mounted on 3.8 cm \times 9.0 cm \times 0.8 mm (t) glass epoxy PWB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Document No. PU10768EJ02V0DS (2nd edition)
Date Published November 2009 NS

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THERMAL RESISTANCE (TA = +25°C)

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Parameter	Symbol	Ratings	Unit
Termal Resistance from Junction to Ambient Note	Rth _{j-a}	260	°C/W

Note Mounted on 3.8 cm \times 9.0 cm \times 0.8 mm (t) glass epoxy PWB

RECOMMENDED OPERATING RANGE ($T_A = +25$ °C)

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Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Collector Current	lc	-	40	-	mA

ELECTRICAL CHARACTERISTICS (TA = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit	
DC Characteristics							
Collector Cut-off Current	Ісво	VcB = 5 V, IE = 0 mA	_	_	100	nA	
Emitter Cut-off Current	ІЕВО	V _{EB} = 0.4 V, I _C = 0 mA	-	-	100	nA	
DC Current Gain	hfE Note 1	VcE = 5 V, Ic = 15 mA	140	180	260	_	
RF Characteristics							
Gain Bandwidth Product	f⊤	VcE = 5 V, Ic = 40 mA, f = 1 GHz	-	10.5	_	GHz	
Insertion Power Gain	S _{21e} ²	VcE = 5 V, Ic = 40 mA, f = 1 GHz	9.5	11.5	_	dB	
Noise Figure (1)	NF1	$V_{\text{CE}} = 5 \text{ V, lc} = 15 \text{ mA, f} = 1 \text{ GHz,}$ $Z_{\text{S}} = Z_{\text{Sopt}}, Z_{\text{L}} = 50 \Omega$	_	0.75	1.15	dB	
Noise Figure (2)	NF2	$V_{CE} = 5 \text{ V, Ic} = 40 \text{ mA, f} = 1 \text{ GHz,}$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$	-	0.8	-	dB	
Associated Gain (1)	Ga1	$V_{CE} = 5 \text{ V, I}_{C} = 15 \text{ mA, f} = 1 \text{ GHz,}$ $Z_{S} = Z_{Sopt}, Z_{L} = 50 \Omega$	9.0	11.0	-	dB	
Associated Gain (2)	G _a 2	$V_{CE} = 5 \text{ V}, \text{ Ic} = 40 \text{ mA}, \text{ f} = 1 \text{ GHz},$ $Z_{S} = Z_{Sopt}, Z_{L} = Z_{Lopt}$	-	12.0	-	dB	
Reverse Transfer Capacitance	Cre Note 2	V _{CB} = 5 V, I _E = 0 mA, f = 1 MHz	_	0.9	1.1	pF	
Maximum Stable Power Gain	MSG Note 3	VcE = 5 V, Ic = 40 mA, f = 1 GHz	11.0	13.0	_	dB	
Gain 1 dB Compression Output Power	Po (1 dB)	$\begin{aligned} &V_{\text{CE}} = 5 \text{ V, Ic}_{\text{(set)}} = 40 \text{ mA, f} = 1 \text{ GHz,} \\ &Z_{\text{S}} = Z_{\text{Sopt, ZL}} = Z_{\text{Lopt}} \end{aligned}$	-	23.5	-	dBm	
Output 3rd Order Intercept Point	OIP ₃	$V_{\text{CE}} = 5 \text{ V, Ic }_{(\text{set})} = 40 \text{ mA, f} = 1 \text{ GHz,}$ $\Delta f = 1 \text{ MHz, Zs} = Z_{\text{Sopt, ZL}} = Z_{\text{Lopt}}$	_	35.5	_	dBm	

Notes 1. Pulse measurement: PW \leq 350 μ s, Duty Cycle \leq 2%

2. Collector to base capacitance when the emitter grounded.

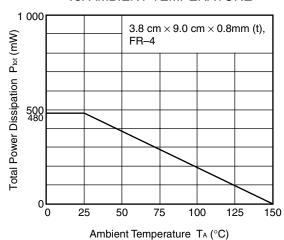
3. MSG =
$$\frac{S_{21}}{S_{12}}$$

hfe CLASSIFICATION

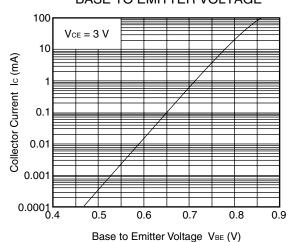
Rank	FB		
Marking	R7A		
h _{FE} Value	140 to 260		

<R> TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

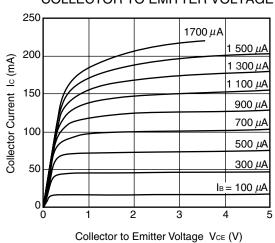
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

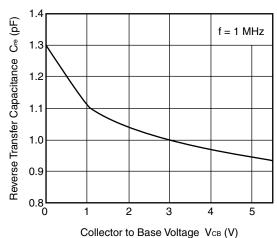


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

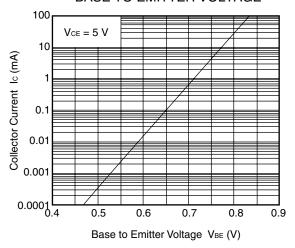


Remark The graphs indicate nominal characteristics.

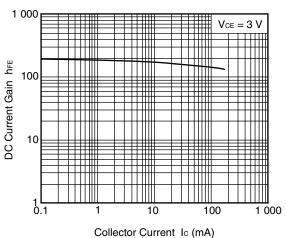
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



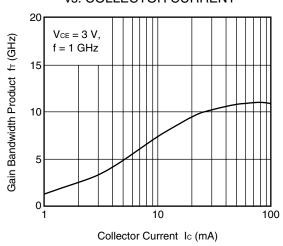
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



DC CURRENT GAIN vs. COLLECTOR CURRENT

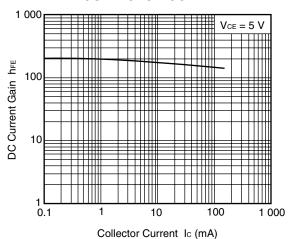


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

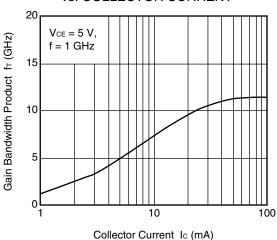


Remark The graphs indicate nominal characteristics.

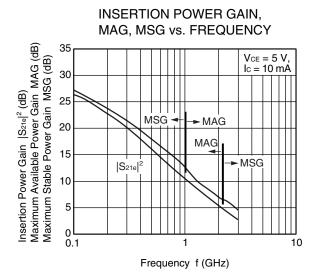
DC CURRENT GAIN vs. COLLECTOR CURRENT

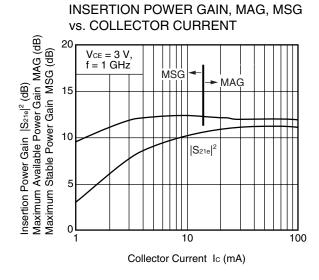


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

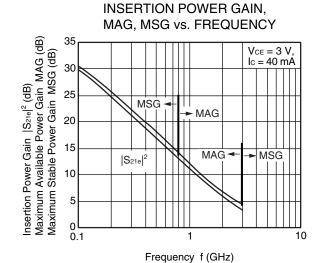


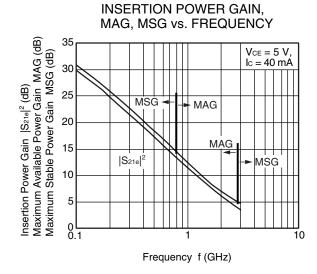
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY Maximum Available Power Gain MAG (dB) Maximum Stable Power Gain MSG (dB) 35 VcE = 3 V, lc = 10 mA 30 Insertion Power Gain |S21e|2 (dB) 25 MAG 20 MAG 15 |S_{21e} MSG 10 5 0.1 10 Frequency f (GHz)

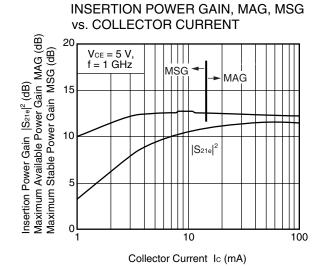




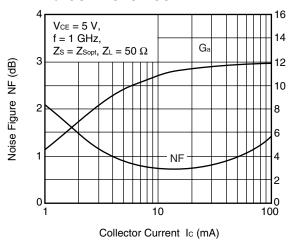
Remark The graphs indicate nominal characteristics.



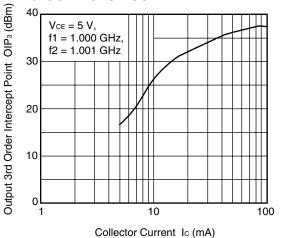




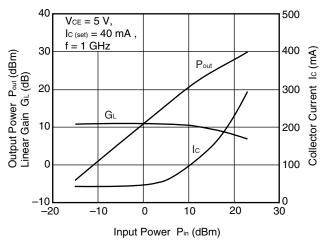
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



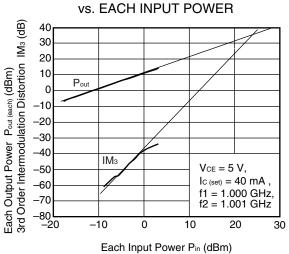
OUTPUT 3RD ORDER INTERCEPT POINT vs. COLLECTOR CURRENT



OUTPUT POWER, LINEAR GAIN, COLLECTOR CURRENT vs. INPUT POWER



EACH OUTPUT POWER, IM3



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

G_a (dB)

Associated Gain

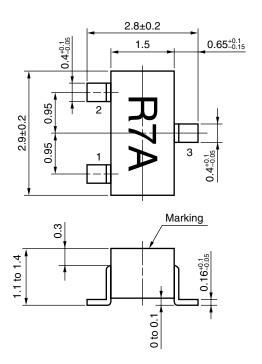
Click here to download S-parameters.

 $[\mathsf{RF} \ \mathsf{and} \ \mathsf{Microwave}] \to [\mathsf{Device} \ \mathsf{Parameters}]$

URL http://www.necel.com/microwave/en/

PACKAGE DIMENSIONS

3-PIN MINIMOLD (33 PKG) (UNIT: mm)



PIN CONNECTIONS

- 1. Emitter
- 2. Base
- 3. Collector

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